Abstract of Disclosure

GATE STRUCTURE AND METHOD OF MAKING THE SAME

A method of making a gate structure includes the following steps. First, a gate is formed. Then, a first silicon oxide layer, a silicon nitride layer, and a second silicon oxide layer are formed to cover the gate from bottom to top. Later, a dry etching is performed to etch the second silicon oxide layer. After that, a wet etching is performed to etch the silicon nitride layer and the first silicon oxide layer. The aforesaid wet etching is performed by utilizing an RCA cleaning solution. Furthermore, the silicon nitride layer is formed by the SINGEN process. Therefore, the first and second silicon oxide layer and the silicon nitride layer can be etched together by the RCA cleaning solution.

Fig. 4